

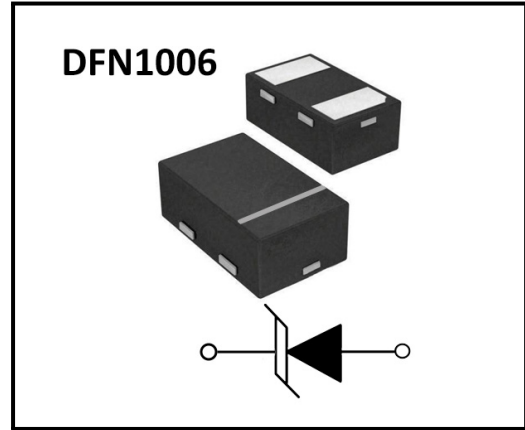
# PESD12VS1UL-N

ESD Protection Diode

## Features

- 250Watts peak pulse power (tp = 8/20µs)
- Unidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping Voltage
- Low leakage current
- Protection one data/power line
- IEC 61000-4-2 ±30kV contact ; ±30kV air
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 10A (8/20µs)

## Package



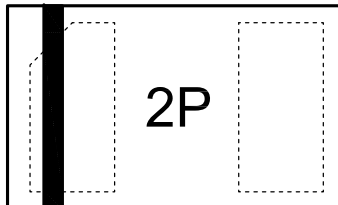
## Applications

- Laptop Computers
- Cellular Phones
- Digital Cameras
- Personal Digital Assistants (PDA's)

## Mechanical Characteristics

- DFN1006 package
- Molding compound flammability rating: UL 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

## Marking



## Ordering information

Order code	Package	Base qty	Delivery mode
PESD12VS1UL-N	DFN1006	10k	Tape and reel

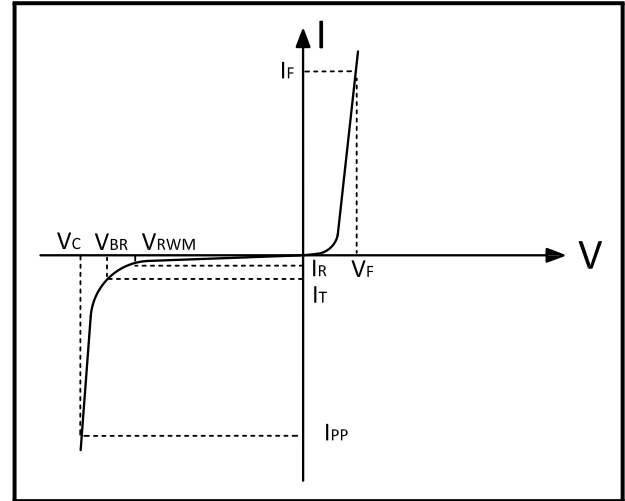


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ESD Protection Diode

## Electrical Parameters ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter
$I_{PP}$	Maximum Reverse Peak Pulse Current
$V_C$	Clamping Voltage @ $I_{PP}$
$V_{RWM}$	Peak Reverse Working Voltage
$I_R$	Reverse Leakage Current @ $V_{RWM}$
$V_{BR}$	Breakdown Voltage @ $I_T$
$I_T$	Test Current



Note: 8/20us pulse Waveform.

## Absolute Maximum Rating

Rating	Symler	Value	Units
Peak Pulse Power ( $t_p = 8/20\mu\text{s}$ )	$P_{PP}$	250	Watts
Peak Pulse Current ( $t_p = 8/20\mu\text{s}$ )	$I_{PP}$	10	A
ESD per IEC 61000-4-2 (Air)	$V_{ESD}$	30	KV
ESD per IEC 61000-4-2 (Contact)		30	
Lead Soldering Temperature	$T_L$	260(10seconds)	$^\circ\text{C}$
Junction Temperature	$T_J$	-55 to + 150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-55 to + 150	$^\circ\text{C}$

## Electrical Characteristics

Parameter	Symler	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	$V_{RWM}$	-	-	-	12	V
Reverse Breakdown Voltage	$V_{BR}$	$I_T = 1\text{mA}$	13.3	-	17.0	V
Reverse Leakage Current	$I_R$	$V_{RWM} = 12\text{V}, T = 25^\circ\text{C}$	-	-	0.2	$\mu\text{A}$
Clamping Voltage	$V_C$	$I_{PP} = 10\text{A}, t_p = 8/20\mu\text{s}$	-	20	25	V
Junction Capacitance	$C_j$	$V_R = 0\text{V}, f = 1\text{MHZ}$	-	70	80	pF
Forward Voltage	$V_F$	$I_F = 10\text{mA}$	-	-	1.2	V



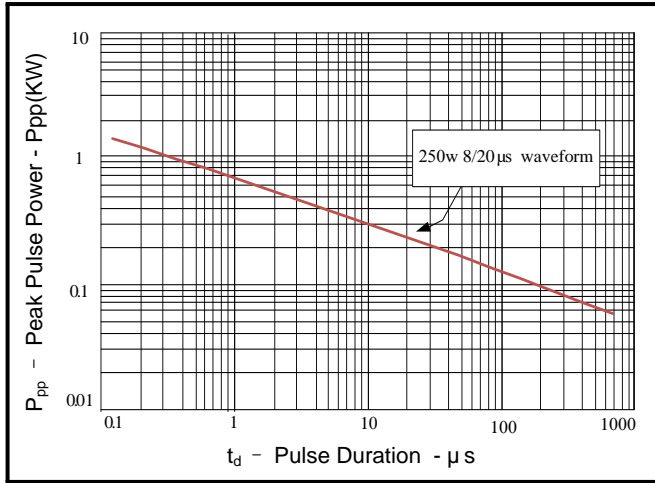


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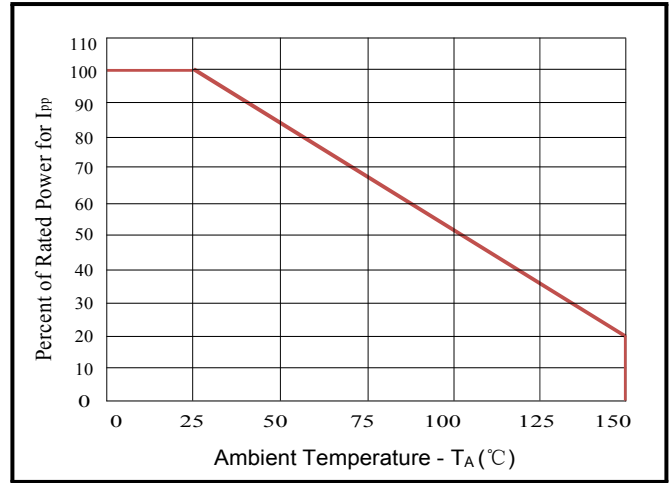
ESD Protection Diode

## Typical Characteristics

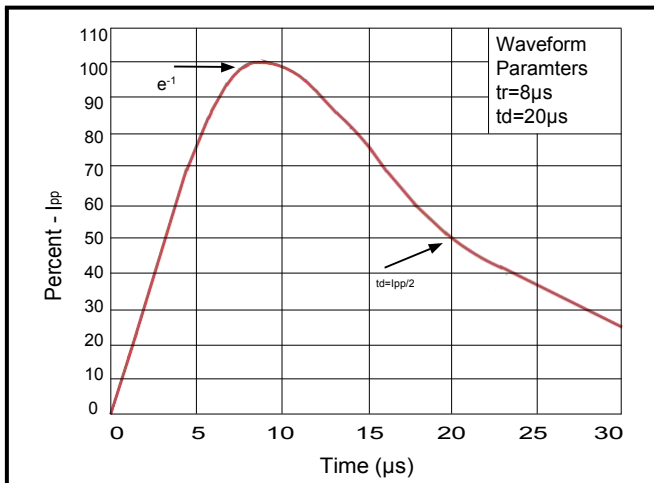
**Figure 1: Peak Pulse Power vs. Pulse Time**



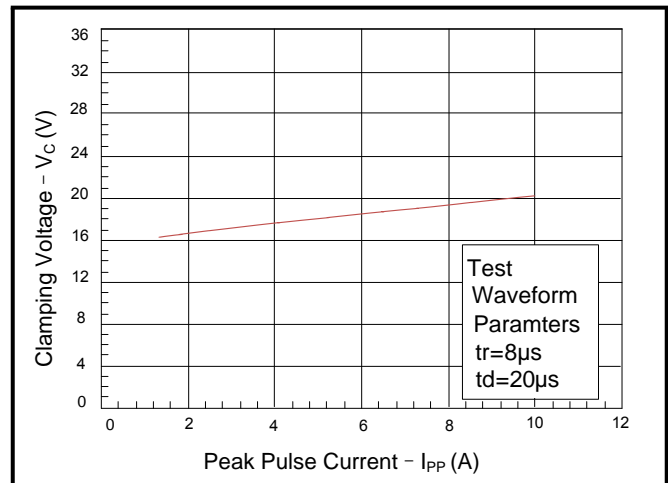
**Figure 2: Power Derating Curve**



**Figure 3: Pulse Waveform**



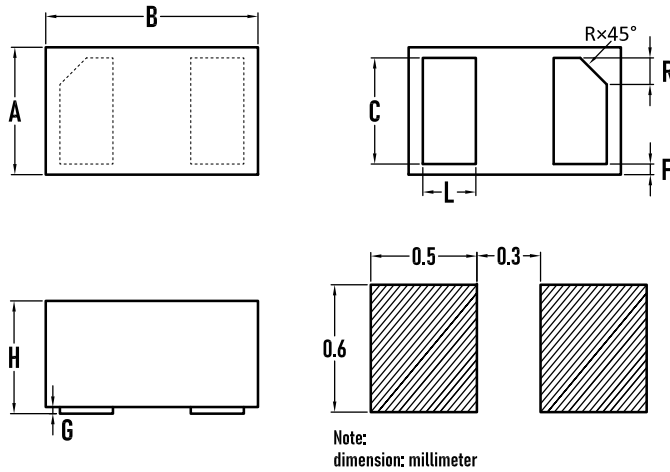
**Figure 4: Clamping Voltage vs. I\_pp**



# PESD12VS1UL-N

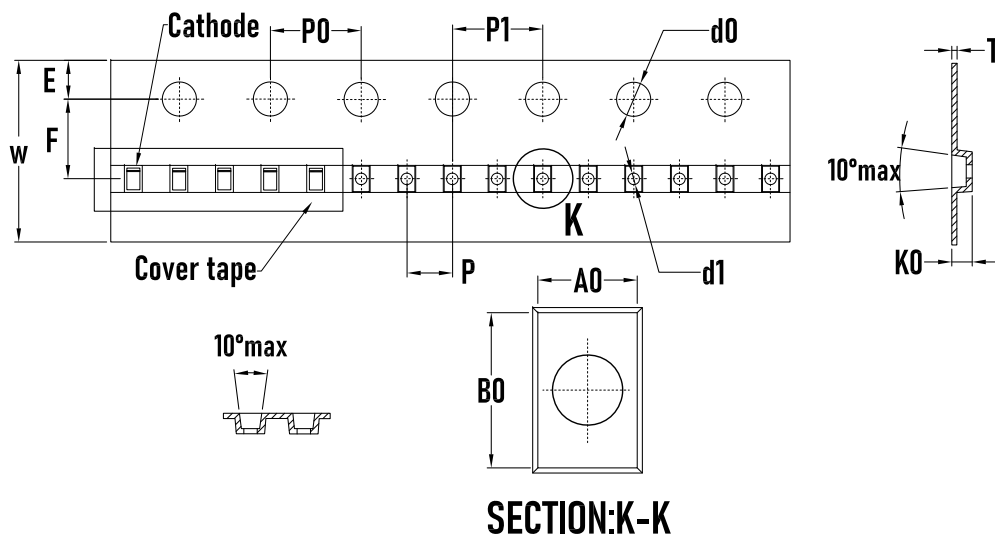
ESD Protection Diode

## Outline Drawing – DFN1006



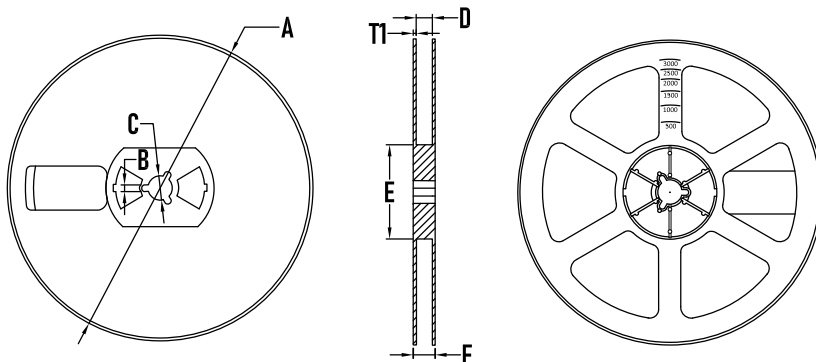
SYMBOL	MILLIMETER		
	MIN.	Typ.	MAX.
A	0.55	0.60	0.65
B	0.95	1.00	1.05
C	0.45	0.50	0.55
L	0.20	0.25	0.30
F	0.05REF		
G	0.00	0.02	0.05
H	0.45	0.50	0.55
R	0.07	0.12	0.17

## Packaging Tape - DFN1006



SYMBOL	MILLIMETER
A0	0.71±0.05
B0	1.11±0.05
d0	1.5 <sup>+0.1</sup> <sub>-0</sub>
d1	0.50±0.05
E	1.75±0.10
F	3.50±0.05
K0	0.56±0.05
P	2.00±0.05
P0	4.00±0.10
P1	2.00±0.05
W	8.00 <sup>+0.03</sup> <sub>-0.01</sub>
T	0.2±0.015

## Packaging Reel



SYMBOL	MILLIMETER
A	178±1
B	3.5±0.2
C	14.3±0.2
D	9.8 <sup>+2</sup> <sub>-1</sub>
E	54.5±0.5
F	12.4±0.2
T1	1.0±0.2
Quantity	10000PCS

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Specifications are subject to change without notice.

Please refer to <http://www.born-tw.com> for current information.

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